)

Substitute Form PTO-1449

U.S. Department of Commerce Patent and Trademark Office

Attorney's Docket No. 07977-004002

Application No.

New Continuation Application 10 60276 L

Information Disclosure Statement by Applicant (Use several sheets if necessary)

Applicant Naoto Kusumoto et al.

Filing Date June 25, 2003

Group Art Unit 2828

C TIBELL			U.S. Pate	ent Documents		120-10	
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
Drfa	AA	3,585,088	06/1971	Scwuttke et al.			/
	AB	4,195,913	4/1/80	Dourte et al.			. /
	AC	4,475,027	10/2/84	Pressley			
	AD	5,145,808	09/1995	Sameshima et al.			
	AE	5,219,786	6/15/93	Noguchi			
	AF	5,304,357	04/1994	Sato et al.			/
	AG	5,365,875	11/1994	Asai et al.			/
	AH	5,424,244	6/13/95	Zhang, et al.			/
	AI	5,432,122	07/1995	Chae			/
	AJ	5,477,073	12/1995	Wakai et al.			
	AK	5,496,768	03/1996	Kudo			
	AL	5,561,081	02/1994	Takenouchi et al.			
	AM	5,591,668	01/1997	Maegawa et al.	:		
	AN	5,643,801	7/1/97	Ishihara, et al.			
	AO	5,795,795	8/18/98	Kousai, et al.		/	
·	AP	5,849,043	12/15/98	Zhang, et al.		/	
	AQ	5,891,764	4/6/99	Ishihara, et al.			
	AR	5,897,799	4/27/99	Yamazaki et al			
	AS	6,143,661	11/7/2000	Kousai, et al.	1/		
SPI	AT	6,358,784	03/19/2002	Zhang, et al	/		-

	Foreig	n Patent Do	cuments or F	Published Foreign	Patent A	Application	าร	
Examiner	Desig.	Document	Publication	Country or			Trans	lation
Initial	ID	Number	Date	Patent Office	Class	Subclass	Yes	No
My	AU	ZA8306334	03/1984	China				
$\perp L$	AV	64-76715	03/1989	Japan				
	AW	1-76715	03/1989	Japan				
Mor	AX	3-286518	12/1991	Japan	1			

Examiner & Ignature	Date Considered
)
Mille Jane	(2/01)
EXAMINER: Initials citation considered. Draw line through citation if no	of in conformance and not considered. Include copy of this form with
next communication to applicant.	or in commence and more assessed incided copy of this follil Milli

Translation

·No

Yes

Attorney's Docket No. Application No. Spessible Form PTO-1449 (Modified) U.S. Department of Commerce 07977-004002 New Continuation Patent and Trademark Office Application 10-602762 Information Disclosure Statement Applicant by Applicant (Use several sheets if necessary) Naoto Kusumoto et al. Filing Date **Group Art Unit** 2828 June 25, 2003 Foreign Patent Documents or Published Foreign Patent Applications Examiner Desig. Document Publication Country or Initial ID Number Date Patent Office Class Subclass

10/1992

AY

4-307727

(Other D	ocuments (include Author, Title, Date, and Place of Publication)
Examiner	Desig.	
Initial ID		Document
Sort	AZ	Anderson et al.; "Characterization of the substrate interface of excimer laser crystallized polysi"; MRS Symp. Proc. 343; pp. 709; 1994
·	AAA	Brotherton et al.; "Beam shape effects with EL crystallization ofa-Si"; Solid State Phenomena 37-38; pp. 299-304; 1994
	ABB	Carluccio et al., "Microstructure of Polycrystalline Silicon Films Obtained by Combined Furnace and Laser Annealing", Appl. Phys. Lett., Vol. 66, No. 11, pp. 1394-1396
	ACC	Caune et al.; "Combined CW laser and furnace annealing of a-Si and Ge in contact with some metals"; Appl. Surf. Sci. 36; p. 597; 1989
	ADD	Hayashi et al.; "Fabrication of Low-Temperature Bottom-Gate Poly-Si TFTs on Large-Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method"; <i>IEEE IEDM</i> ; pp. 829-832; 1995
	AEE	Jhon et al.; "Crystallization of Amorphous Silicon by Excimer Laser Annealing with a Line Shape Beam Having a Gaussian Profile"; Japan Journal of Applied Physics, Vol. 33; pp. 1438-1441; October 1994
	AFF	Jhon et al.; "Crystallization of a-Si by ELA with a line shape beam having a Gaussian profile"; Jpn. J. Appl. Phys 33(10B); p. L1438; October 1994
	AGG	Kohno et al., "High Performance Poly-Si TFTs Fabricated Using Pulsed Laser Annealing and Remote Plasma CVD with Low Temperature Processing", IEEE Transactions on Electron Devices, Vol. 42, No. 2, pp. 251-257
	АНН	Kuriyama et al.; "ImprovingELA method for giant microelectronics"; Jpn. J. Appl. Phys. 31(12B); p. 4550; December 1992
	AII	Kuriyama et al.; "Lateral growth of Poly-Si filmsby ELA"; Jpn. J. Appl. Phys. 32(12B); p. 6190; December 1993
	AJJ	Okumura et al.; "Excimer laser annealed poly-Si TFT technologies"; MRS Symp. Proc. 377; p. 877; April 1995
DA	AKK	Sweatt; "Transforming a circular laser beam into a square or trapezoid"; Optical Eng. 31(2); p. 245: February 1992

Japan

Examiner Signature	Date Considered
Anskie Jona	12/00
EXAMINER: Initials chatton considered. Draw line through citation if no	ot in conformance and not considered. Include copy of this form with
next communication to applicant.	
	Substitute Disclosure Form (PTO-1449)

Substitute Form PTO-1449 (Modified)

U.S. Department of Commerce Patent and Trademark Office

Attorney's Docket No. 07977-004002

Application No. New Continuation

Application QU2762

Information Disclosure Stat m nt by Applicant (Use several sheets if necessary)

(37 CFR §1.98(b))

Applicant Naoto Kusumoto et al.

Filing Date
June 25, 2003

Group Art Unit

			U.S. Pate	ent Documents			
Examine Initial	r Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
DA	AA	3,585,088	06/1971	Scwuttke et al.			/
	AB	4,195,913	4/1/80	Dourte et al.			
	AC	4,475,027	10/2/84	Pressley			
	AD	5,145,808	09/1995	Sameshima et al.			
	ĄĒ	5,219,786	6/15/93	Noguchi			
	AF	5,304,357	04/1994	Sato et al.			
	AG	5,365,875	11/1994	Asai et al.			
	АН	5,424,244	6/13/95	Zhang, et al.			
	AI	5,432,122	07/1995	Chae			/
	AJ	5,477,073	12/1995	Wakai et al.			
	AK	5,496,768	03/1996	Kudo			
	AL	5,561,081	02/1994	Takenouchi et al.			
	AM	5,591,668	01/1997	Maegawa et al.			
	ÀN	5,643,801	7/1/97	Ishihara, et al.			
	AO	5,795,795	8/18/98	Kousai, et al.		1	
	AP	5,849,043	12/15/98	Zhang, et al.			
	AQ	5,891,764	4/6/99	Ishihara, et al.			
	AR .	5,897,799	4/27/99	Yamazaki et al			
	AS	6,143,661	11/7/2000	Kousai, et al.			
DIA	AT	6,358,784	03/19/2002	Zhang, et al			

	Foreig	n Patent Do	cuments or F	Published Foreign F	Patent /	Applicatio	ns	
Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Trans Yes	slation ≣No≣
Dod	AU	ZA8306334	03/1984	China				
	AV	64-76715	03/1989	Japan				
	AW	1-76715	03/1989	Japan				
Drive	AX	3-286518	12/1991	Japan			 	

Examinat 8 gna	ture	<u></u>	
Horse	The .	e Bort	an
EVAMINED: In	043	T Soppido	od Draw line

Date Considered

line through citation if not in conformance and not considered. Include copy of this form with

next communication to applicant.

Application No. Attorney's Docket No. Substitute Form PTO-1449 U.S. Department of Commerce Patent and Trademark Office New Continuation 07977-004002 (Modified) Application 10-1112761 Information Disclosur Statem nt Applicant by Applicant Naoto Kusumoto et al. (Use several sheets if necessary) Filing Date (37 CFR §1.98(b)) June 25, 2003 Foreign Patent Documents or Published Foreign Patent Applications Desig. Document · Country or Publication Examiner Translation Initial ID Number Patent Office Date Class Subclass Yes No

Japan

AY

4-307727

10/1992

Ι.		Other D	ocuments (include Author, Title, Date, and Place of Publication)
Exa	aminer	Desig.	
!	nitial	ID	Document
DY	M	AZ	Anderson et al.; "Characterization of the substrate interface of excimer laser crystallized polysi"; MRS Symp. Proc. 343; pp. 709; 1994
		AAA	Brotherton et al.; "Beam shape effects with EL crystallization ofa-Si"; Solid State Phenomena; pp. 37-38; 1994
		ABB	Carluccio et al., "Microstructure of Polycrystalline Silicon Films Obtained by Combined Furnace and Laser Annealing", Appl. Phys. Lett., Vol. 66, No. 11, pp. 1394-1396
		ACC	Caune et al., "Combined CW laser and furnace annealing of a-Si and Ge in contact with some metals"; Appl. Surf. Sci. 36; p. 597; 1989
			Hayashi et al.; "Fabrication of Low-Temperature Bottom-Gate Poly-Si TFTs on Large-Area
	·	. ADD	Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method"; IEEE IEDM; pp.
			829-832; 1995
		AEE	Jhon et al.; "Crystallization of Amorphous Silicon by Excimer Laser Annealing with a Line Shape Beam Having a Gaussian Profile"; Japan Journal of Applied Physics, Vol. 33; pp. 1438-1441; October 1994
		AFF	Jhon et al.; "Crystallization of a-Si by ELA with a line shape beam having a Gaussian profile"; Jpn. J. Appl. Phys 33(10B); p. L1438; October 1994
		AGG	Kohno et al., "High Performance Poly-Si TFTs Fabricated Using Pulsed Laser Annealing and Remote Plasma CVD with Low Temperature Processing", IEEE Transactions on Electron Devices, Vol. 42, No. 2, pp. 251-257
		АНН	Kuriyama et al.; "ImprovingELA method for giant microelectronics"; Jpn. J. Appl. Phys. 31(12B); p. 4550; December 1992
		AII	Kuriyama et al., "Lateral growth of Poly-Si filmsby ELA"; Jpn. J. Appl. Phys. 32(12B); p. 6190; December 1993
		AJJ	Okumura et al.; "Excimer laser annealed poly-Si TF1 technologies"; MRS Symp. Proc. 377; p. 877; April 1995
Si	X	AKK	Sweatt; "Transforming a circular laser beam into a square or trapezoid"; Optical Eng. 31(2); p. 245; February 1992

Examiner Signature (Date Considered
$\mathcal{L}_{n}(\mathcal{S}(\mathcal{I}))$	
Horkus Ilno	12-104
EXAMINER: Initials citation considered. Draw line through citation if n	of in conformance and not considered. Include conv of this form with
next communication to applicant.	over companies and not considered include copy of this family will

31		c	1
Sheet	1 0	ı	1

ENT &	Substitute Form PTO-1449 TRADE (Ned)
-------	---

(37 CFR §1.98(b))

U.S. Department of Commerce Patent and Trademark Office Attorney's Docket No. 07977-004002

Application No. 10/602,762

Information Disclosure Statement by Applicant

(Use several sheets if necessary)

Applicant Naoto Kusumoto et al.

Filing Date
June 25, 2003

Group Art Unit

			U.S. Patent	Documents			
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE					. <u>.</u>	
	AF						
	AG						
	AH						
	AI						

	Foreign	Patent Doo	uments or Pu	blished Foreign	Patent A	Application	าร	
Examiner	Desig.	Document	Publication	Country or			Translation	
Initial	ID	Number	Date	Patent Office	Class	Subclass	Yes	No
	AJ							
	AK							
	AL							
	AM							
	AN							<u> </u>

	Other Documents (include Author, Title, Date, and Place of Publication)							
Examiner Initial	Desig. ID	Document						
Juga	AO	Brotherton et al.; "Beam shape effects with EL crystallization ofa-Si"; Solid State Phenomena, Vol. 37-38; pp. 209-304; 1994						

Examiner Signature	Date Considered
flux Ruiscellone on	12/00
EXAMINER: Initials citation considered. Draw line through citation if no	t in conformance and not considered. Include copy of this form with

next communication to applicant.

Substitute Form PTO-1449 (Modified) U.S. Department of Paper at and Trades	Commerce Attorney's I 07977-0		Application No. 10/602,762	
Information Disclosure Statement by Applicant	, Applicant	Lusumoto et al.		
(Use several sheets if necessary) (37 CFR §1.98(b))	Filing Date June 25,		Group Art Unit 2828	

	U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate	
DAR	AA	2003/0015133	01/23/2003	ZHANG et al.			08/22/2002	
	AB	2003/0207524	11/06/2003	ZHANG et al.		/	06/04/2003	
	AC	5,352,291	10/04/1994	ZHANG et al.			08/11/1993	
	AD	5,578,520	11/26/1996	ZHANG et al.			07/15/1994	
	AE	5,766,344	06/16/1998	ZHANG et al.			05/26/1995	
	AF	5,861,337	01/19/1999	ZHANG et al.			06/02/1995	
	AG	6,174,374	01/16/2001	ZHANG et al.			09/26/1996	
	AH	6,494,162	12/17/2002	ZHANG et al.			10/25/2000	
	AI	6,576,534	06/10/2003	ZHANG et al.	17		02/10/1998	
	AJ	6,770,143	08/03/2004	ZHANG et al.			08/22/2002	
Spil	AK				1			

	Foreig	n Patent Do	cuments or P	ublished Foreign	Patent A	Applica	tions	
Examiner	Desig.	Document	Publication	Country or		Sub-	Transla	'
Initial	_ ID	Number	Date	Patent Office	Class	class	Yes	No
Word	AL	JP05-182923	23 JUL 1993	JAPAN	4		Abstract	
Work	AM	JP05-198507	06 AUG 1993	JAPAN			Abstract	
	AN							
	AO							
	AP							

	Other Documents (include Author, Title, Date, and Place of Publication)							
Examiner Initial	Desig. ID	Document						
	AQ							
	AR							
	AS							
	AT							

Examiner Signature	Date Considered
This Kur word on	12/0K
EXAMINER: Initials citation considered. Draw line through citation if n	ot in conformance and not considered. Include copy of this form with
next communication to applicant	

DEC 0 1 2003

Substitute Form PTO 1849
(Modified)
U.3 Department of Commerce Patent and Trademark Office
Information Disclosure Statement

Attomey's Docket No. 07977-004002

Application No. 10/602,762

by Applicant (Use several sheets if necessary)

Applicant Naoto Kusumoto et al.

Filing Date
June 25, 2003

Group Art Unit 2828

(37 CFR §1.98(b))

			U.S. Pate	ent Documents			
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
Drou	AA	5,569,610	10/29/1996	Zhang et al.			03/08/1994
Sva	AB	5,614,733	03/25/1997	Zhang et al.			12/12/1994
Door	AC	5,783,468	07/21/1998	Zhang et al.			04/10/1996
	AD						
	AE						•
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

	Foreig	n Patent Do	cuments or F	Published Foreign	Patent A	Application	ns	
Examiner	Desig.	Document	Publication	Country or			Trans	lation
Initial	ID	Number	Date	Patent Office	Class	Subclass	Yes	No
infor	AL	02-224346	09/06/1990	JAPAN			ABS	
NOC	AM	06-318701	11/15/1994	JAPAN			ABS	
DAN	AN	08-051074	02/20/1996	JAPAN			ABS	
	AO							
	AP							

	Other Documents (include Author, Title, Date, and Place of Publication)						
Examiner Initial	Desig. ID	Document					
	AQ						
	AR						
	AS	·					
	AT	·					

Examiger Signature	Date Considered
Harris Incan	12/14
4 My Kus Son & an	
EXAMINER! Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with	
next communication to applicant.	
	Substitute Disclosure Form (PTO-1449)